

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 14603-0007US1	Application No. 10/500,079
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))		Applicant Jochen Kraft et al.	
		Filing Date March 1, 2005	Group Art Unit 2814

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
/A.M./	1						
	2						
	3						
	4						
	5						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
/A.M./	6							
	7							
	8							
	9							
	10							

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
/A.M./	11	Greve, D., "Growth of Epitaxial Germanium- Silicon Heterostructures by Chemical Vapour Deposition", Material Science and Engineering, B18, pp. 22-51 (1993).
/A.M./	12	Lanzerotti, L. D. et al.: "Suppression of Boron Outdiffusion in SiGe HBTs by Carbon Incorporation", IEEE 1996, 0-7803-3393-4.
	13	Osten, H. J. et al.: "Substitutional Versus Interstitial Carbon Incorporation During Pseudomorphic Growth of Si1-yCy on Si(OO1)", Journal of Applied Physics, vol. 80(12), pp. 6711-6715 (1996).
	14	Zerlauth, S. et al.: "Growth Conditions for Complete Substitutional Carbon Incorporation into Si1-yCy Layers Grown by Molecular Beam Epitaxy", Applied Physics Letters, vol. 71(26), pp. 3826-3828 (1997).

Examiner Signature /Anh Mai/	Date Considered 07/20/2009
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EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.